

## **AXIAL LEADED SILICON RECTIFIER DIODE**

VOLTAGE RANGE: 1300V CURRENT: 1.0 A

## **Features**

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

## **Mechanical Data**

Case: D O - 4 1 Molded Plastic

• Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208

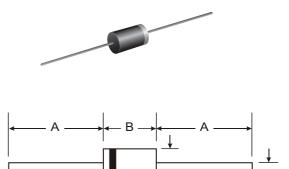
Polarity: Cathode Band

Weight: 0.34 grams (approx.)

Mounting Position: Any

Marking: Type Number





	DO-41		
Dim	Min	Max	
Α	25.40	_	
В	4.06	5.21	
С	0.71	0.864	
D	2.00	2.72	
All Dimensions in mm			

## Maximum Ratings and Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	BY133	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	1300	V
RMS Reverse Voltage	VR(RMS)	910	V
Average Rectified Output Current (Note 1) @T <sub>A</sub> = 75°C	lo	1.0	А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	30	А
Forward Voltage @I <sub>F</sub> = 1.0A	VFM	1.0	V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	IRM	5.0 50	μA
Typical Junction Capacitance (Note 2)	Cj	15	pF
Typical Thermal Resistance Junction to Ambient (Note 1)	RθJA	50	K/W
Operating Temperature Range	Tj	-65 to +125	°C
Storage Temperature Range	Тѕтс	-65 to +150	°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.



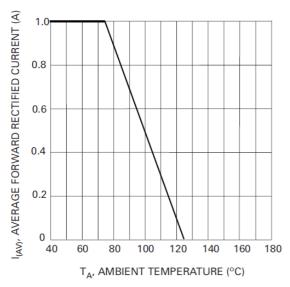
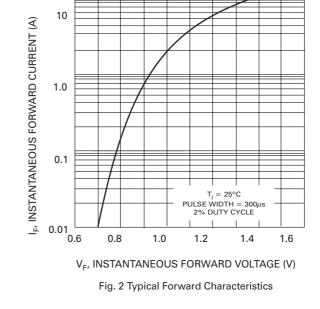


Fig. 1 Forward Current Derating Curve



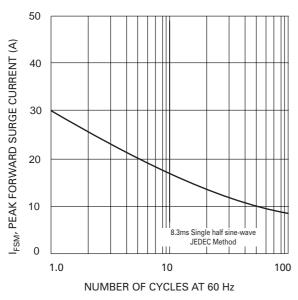


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

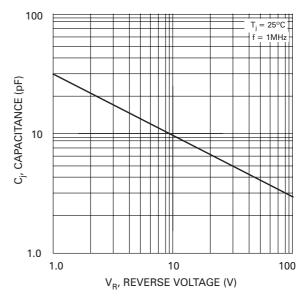


Fig. 4 Typical Junction Capacitance